

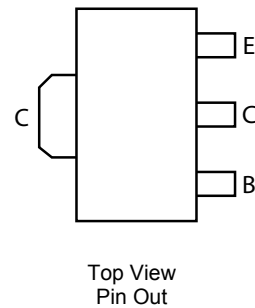
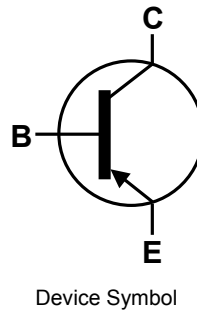
25V PNP MEDIUM POWER TRANSISTOR IN SOT89

Features

- $BV_{CEO} > -25V$
- $I_C = -3A$ high Continuous Current
- $I_{CM} = -8A$ Peak Pulse Current
- Low saturation voltage $V_{CE(sat)} < -320mV @ -3A$
- h_{FE} specified up to -8A for high current gain hold up
- Complementary NPN Type: FCX688B
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT89
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.05 grams (Approximate)

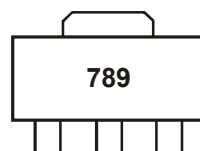


Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX789ATA	789	7	12	1,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



789 = Product Type Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	I _C	-3	A
Peak Pulse Current	I _{CM}	-8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

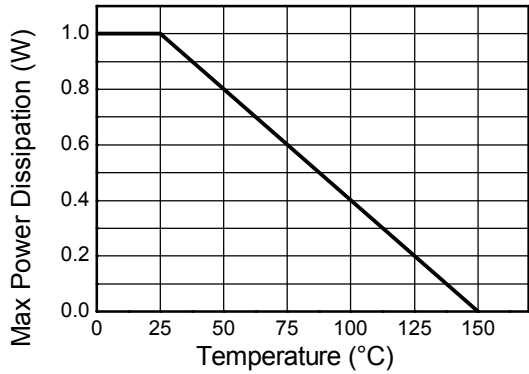
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	(Note 5) 1	W
		(Note 6) 2	
Thermal Resistance, Junction to Ambient Air	R _{θJA}	(Note 5) 125	°C/W
		(Note 6) 62.5	
Thermal Resistance, Junction to Leads	R _{θJL}	5.31	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

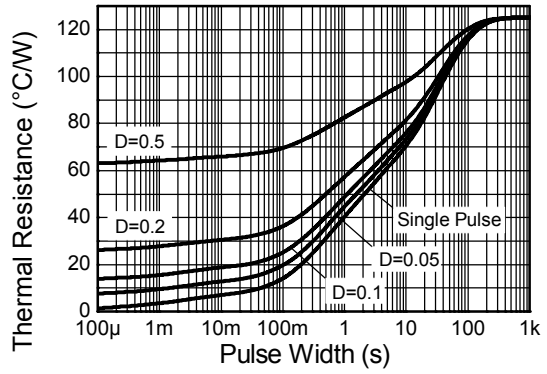
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
5. For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in steady state condition.
 6. Same as note (5), except the device is mounted on 40mm X 40mm FR4 PCB.
 7. Thermal resistance from junction to solder-point (at the end of collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

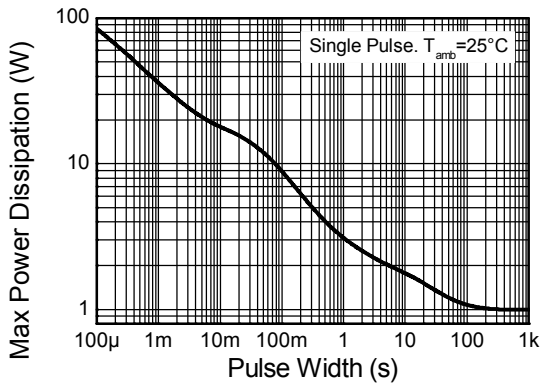
Thermal Characteristics and Derating Information



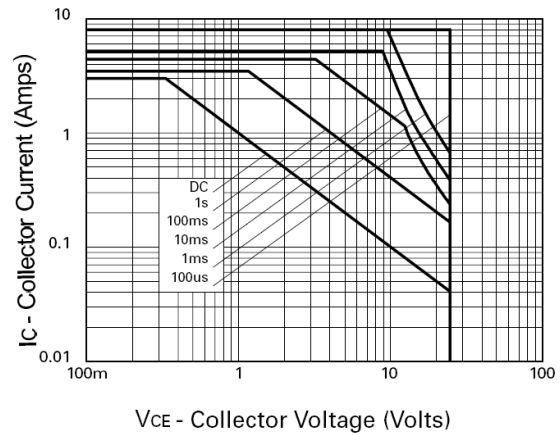
Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



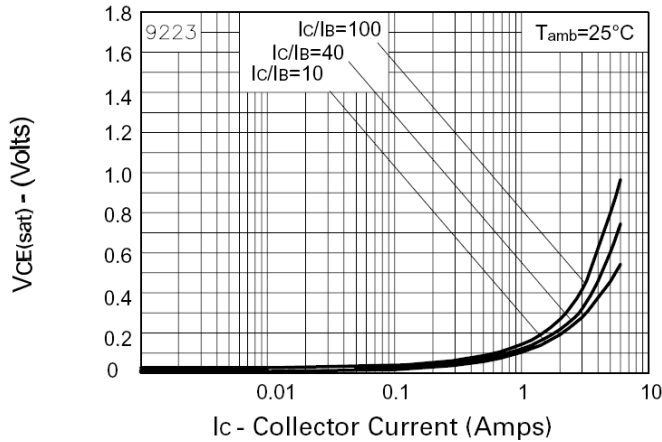
Safe Operating Area

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

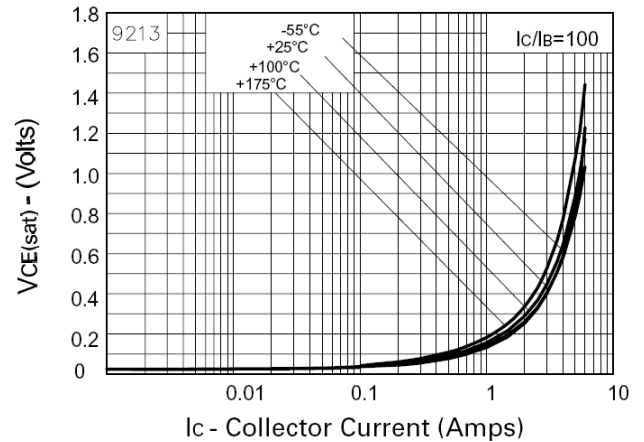
Characteristic	Symbol	Min	Typ.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-25	-	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-25	-	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	-	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	-	<1	-100	nA	V _{CB} = -15V
Emitter Cutoff Current	I _{EBO}	-	<1	-100	nA	V _{EB} = -5.6V
DC current transfer Static ratio (Note 9)	h _{FE}	300 230 180 75	500 320 250 120	800 - - -	-	I _C = -10mA, V _{CE} = -2V I _C = -1A, V _{CE} = -2V I _C = -2A, V _{CE} = -2V I _C = -6A, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	- - -	-130 -290 -250	-190 -400 -320	mV	I _C = -1A, I _B = -10mA I _C = -2A, I _B = -20mA I _C = -3A, I _B = -100mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	-	-0.8	-0.9	V	I _C = -1A, I _B = -10mA
Base-Emitter Turn-on Voltage (Note 9)	V _{BE(on)}	-	-0.8	-	V	I _C = -1A, V _{CE} = -2V
Transitional Frequency	f _T	100	-	-	MHz	I _C = -50mA, V _{CE} = -5V f = 50MHz
Input capacitance	C _{ibo}	-	225	-	pF	V _{EB} = -0.5V, f = 1MHz,
Output capacitance	C _{obo}	-	25	-	pF	V _{CB} = -10V, f = 1MHz,
Switching times	t _{on}	-	35	-	nS	I _C = -500mA, V _{CC} = -10V I _{B1} = -I _{B2} = -50mA
	t _{off}	-	400	-	nS	

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

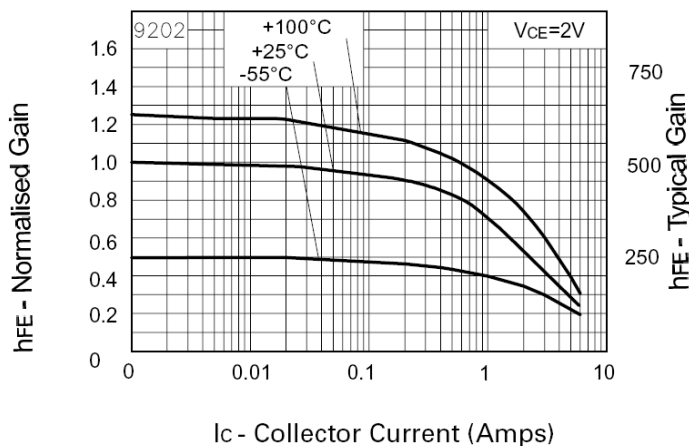
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



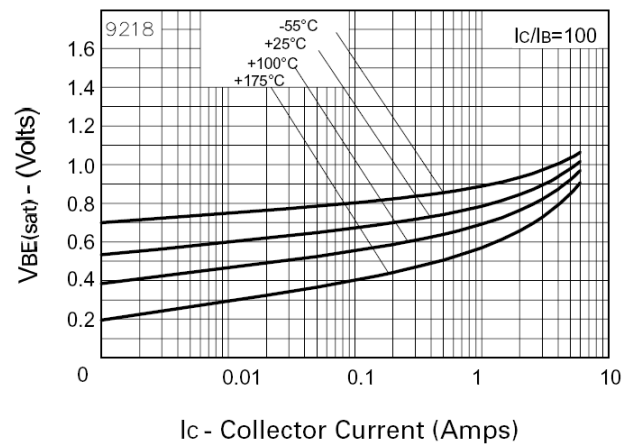
VCE(sat) v IC



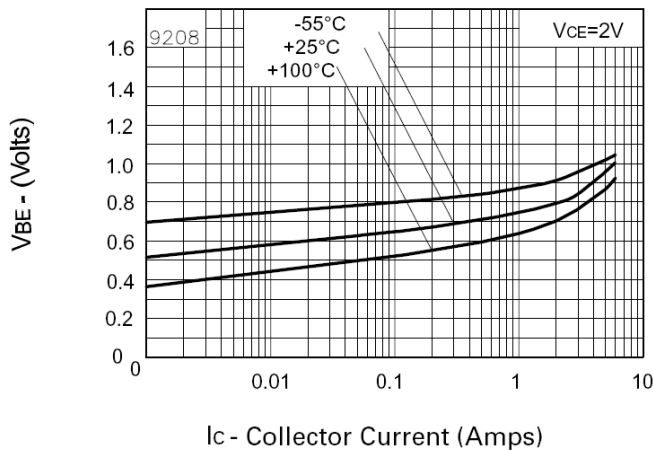
VCE(sat) v IC



hFE v IC



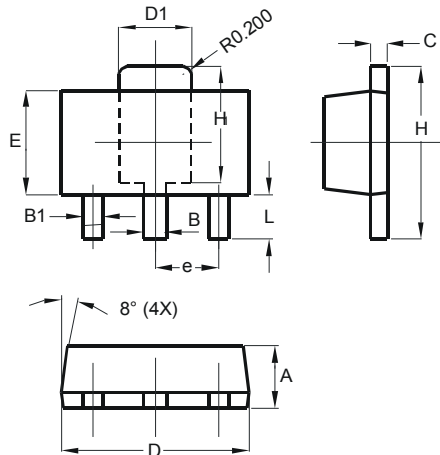
VBE(sat) v IC



VBE(on) v IC

Package Outline Dimensions

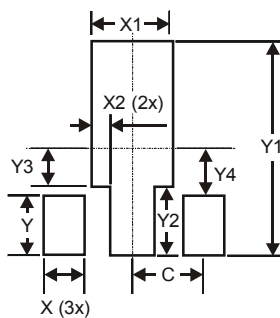
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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